# MSKSEMI 美森科













**ESD** 

71/5

TSS

MOV

**GDT** 

PIFD

# RCLAMP0524J-MS

**Product specification** 





#### **Features**

- 70Watts peak pulse power (tp = 8/20µs)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.2pF typ. I/O to I/O)
- IEC 61000-4-2 ±20kV contact ±25kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4.5A (8/20µs)

#### **Mechanical Data**

- Tiny DFN2710(2.7mmx1.0mm) package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

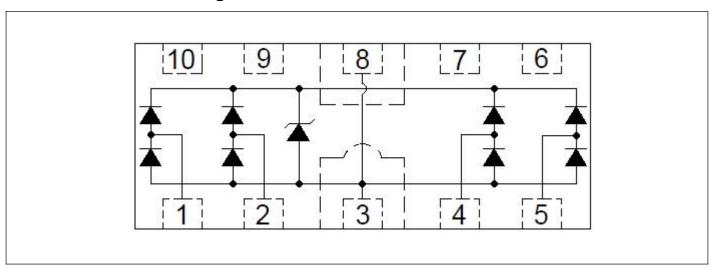
### **Applications**

- USB3.0, USB2.0, Ethernet
- HDMI 2.0, Displayport 1.3,eSATA
- Unified Display interface
- Digital Visual Interface
- High speed serial interface

#### **Reference News**



## **Schematic & PIN Configuration**





# **Absolute Maximum Rating**

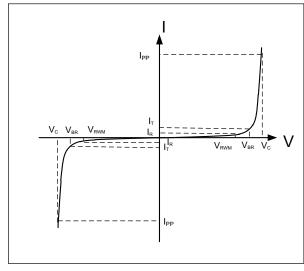
Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>p</sub> =8/20µs )	P <sub>PP</sub>	70	Watts
Peak Pulse Current ( t <sub>p</sub> =8/20μs ) (note1)	I <sub>PP</sub>	4.5	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	25 20	kV
Lead Soldering Temperature	T∟	260(10seconds)	${\mathbb C}$
Junction Temperature	TJ	-55 to + 125	${\mathbb C}$
Storage Temperature	T <sub>stg</sub>	-55 to + 125	${\mathbb C}$

## **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6.0			٧
Reverse Leakage Current	l <sub>R</sub>	V <sub>RWM</sub> =5V,T=25℃			1	μΑ
Peak Pulse Current	I <sub>PP</sub>	tp =8/20μs			4.5	Α
Clamping Voltage	Vc	I <sub>PP</sub> =4A,t <sub>p</sub> =8/20μs			15	V
Junction Capacitance	C <sub>j</sub>	V <sub>R</sub> = 0V, f = 1MHz I/O to I/O		0.2	0.3	pF
		V <sub>R</sub> = 0V, f = 1MHz I/O to GND		0.4	0.55	

# Electrical Parameters (TA = 25°C unless otherwise noted)

	Parameter
<b>I</b> PP	MaximumReversePeak Pulse Current
Vc	Clamping Voltage @ IPP
VRWM	WorkingPeak Reverse Voltage
<b>l</b> R	Maximum Reverse Leakage Current @ VRWM
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
Ь	Test Current



Note:.8/20  $\mu s$  pulse waveform



## **Typical Characteristic Curves**

Fig.1 Peak Pulse Power Rating Curve

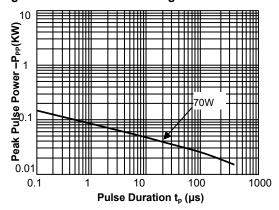


Fig.3 Pulse Waveform-8/20µs

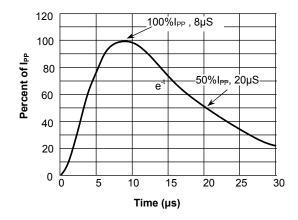


Fig.2 Pulse Derating Curve

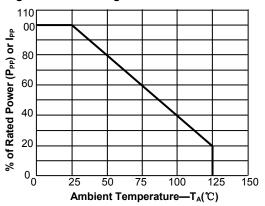
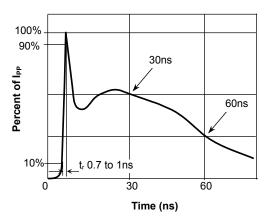
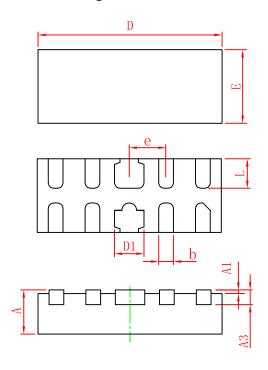


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)





# OutlineDrawing-SLP2710P8



Symbol	Dimensions in millimeters			
Symbol	Min	Nom	Max	
Α	0.38	0.50	0.58	
A1	-	0.02	0.05	
A3	0.10	0.13	0.20	
D	2.60	2.70	2.80	
Е	0.90	1.00	1.10	
D1	0.35	0.40	0.45	
b	0.15	0.20	0.25	
е	0.60BSC			
L	0.30	0.38	0.45	

## **Order information**

Orderable Device	Package	Packing Option
RCLAMP0524J-MS	SLP2710P8	3000PCS



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